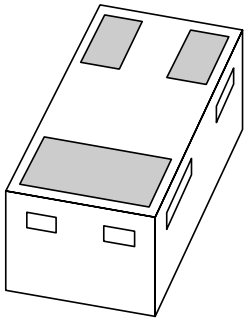
DATA SHEET



PBSS3515M

15 V, 0.5 A

PNP low V_{CEsat} (BISS) transistor

Product data sheet

2003 Jul 22

15 V, 0.5 A PNP low V_{CEsat} (BISS) transistor

PBSS3515M

FEATURES

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency leading to reduced heat generation
- Reduced printed-circuit board requirements.

APPLICATIONS

- Power management:
  - DC-DC converter
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- Peripheral driver:
  - Driver in low supply voltage applications (e.g. lamps and LEDs).
  - Inductive load drivers (e.g. relays, buzzers and motors).

DESCRIPTION

Low V_{CEsat} PNP transistor in a SOT883 leadless ultra small plastic package.
NPN complement: PBSS2515M.

MARKING

TYPE NUMBER	MARKING CODE
PBSS3515M	DB

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	−15	V
I_C	collector current (DC)	−500	mA
I_{CM}	peak collector current	−1	A
R_{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

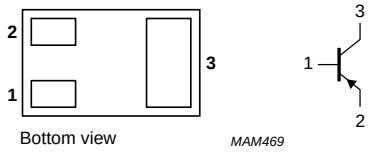


Fig.1 Simplified outline (SOT883) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–15	V
V_{CEO}	collector-emitter voltage	open base	–	–15	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)	notes 1 and 2	–	–500	mA
I_{CM}	peak collector current		–	–1	A
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; notes 1 and 2	–	250	mW
		$T_{amb} \leq 25$ °C; note 1 and 3	–	430	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to SOT883 standard mounting conditions.
2. Device mounted on an FR4 printed-circuit board, single-sided copper, tinplated, standard footprint, with 60 μm copper strip line.
3. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; notes 1 and 2	500	K/W
		in free air; notes 1, 3 and 4	290	K/W

Notes

1. Refer to SOT883 standard mounting conditions.
2. Device mounted on an FR4 printed-circuit board, single-sided copper, tinplated, standard footprint, with 60 μm copper strip line.
3. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2.
4. Operated under pulsed conditions: duty cycle $\delta \leq 20\%$, pulse width $t_p \leq 30$ ms.

Soldering

Reflow soldering is the only recommended soldering method.

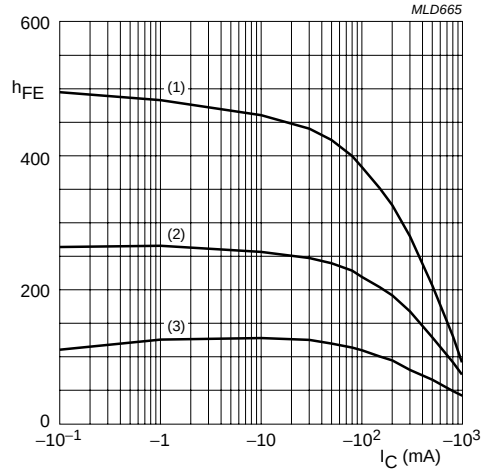
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –15 V; I_E = 0	–	–	–100	nA
		V_{CB} = –15 V; I_E = 0; T_j = 150 °C	–	–	–50	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–	–100	nA
h_{FE}	DC current gain	V_{CE} = –2 V; I_C = –10 mA	200	–	–	
		V_{CE} = –2 V; I_C = –100 mA; note 1	150	–	–	
		V_{CE} = –2 V; I_C = –500 mA; note 1	90	–	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –0.5 mA	–	–	–25	mV
		I_C = –200 mA; I_B = –10 mA; note 1	–	–	–150	mV
		I_C = –500 mA; I_B = –50 mA; note 1	–	–	–250	mV
R_{CEsat}	equivalent on-resistance	I_C = –500 mA; I_B = –50 mA; note 1	–	300	<500	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = –500 mA; I_B = –50 mA; note 1	–	–	–1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = –2 V; I_C = –100 mA; note 1	–	–	–0.9	V
f_T	transition frequency	I_C = –100 mA; V_{CE} = –5 V; f = 100 MHz	100	280	–	MHz
C_c	collector capacitance	V_{CB} = –10 V; I_E = I_e = 0; f = 1 MHz	–	–	10	pF

Note

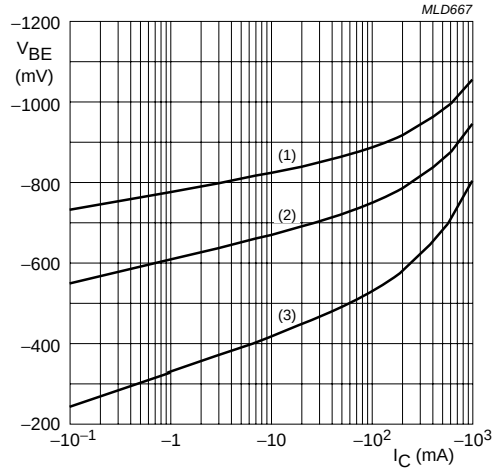
1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



V_{CE} = −2 V.

(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

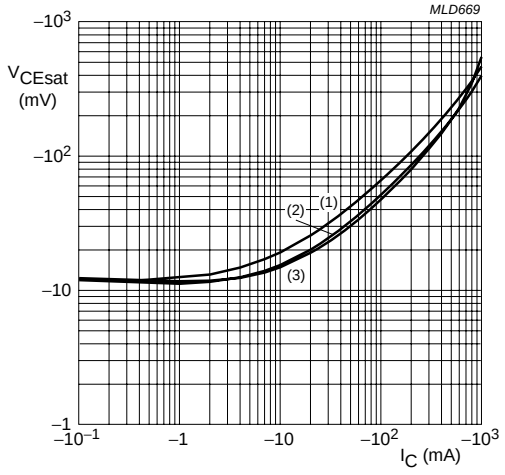
Fig.2 DC current gain as a function of collector current; typical values.



V_{CE} = −2 V.

(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

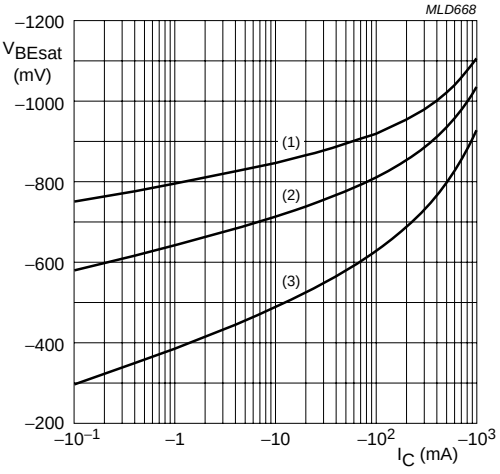
Fig.3 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.

(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

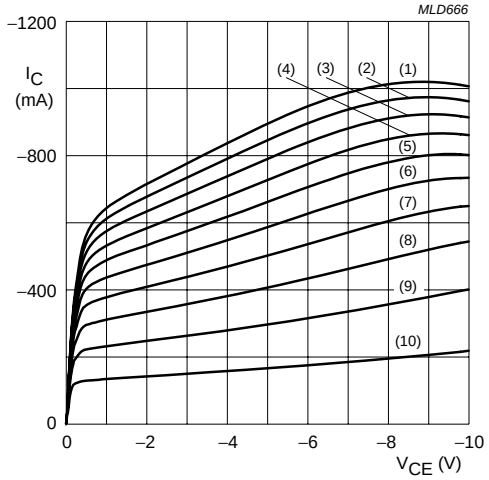
Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



I_C/I_B = 20.

(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

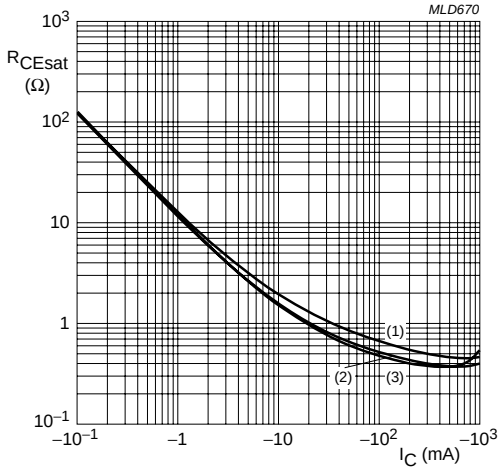
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



T_{amb} = 25 °C.

(1) I_B = −7 mA.
(2) I_B = −6.3 mA.
(3) I_B = −5.6 mA.
(4) I_B = −4.9 mA.
(5) I_B = −4.2 mA.
(6) I_B = −3.5 mA.
(7) I_B = −2.8 mA.
(8) I_B = −2.1 mA.
(9) I_B = −1.4 mA.
(10) I_B = −0.7 mA.

Fig.6 Collector current as a function of collector-emitter voltage; typical values.



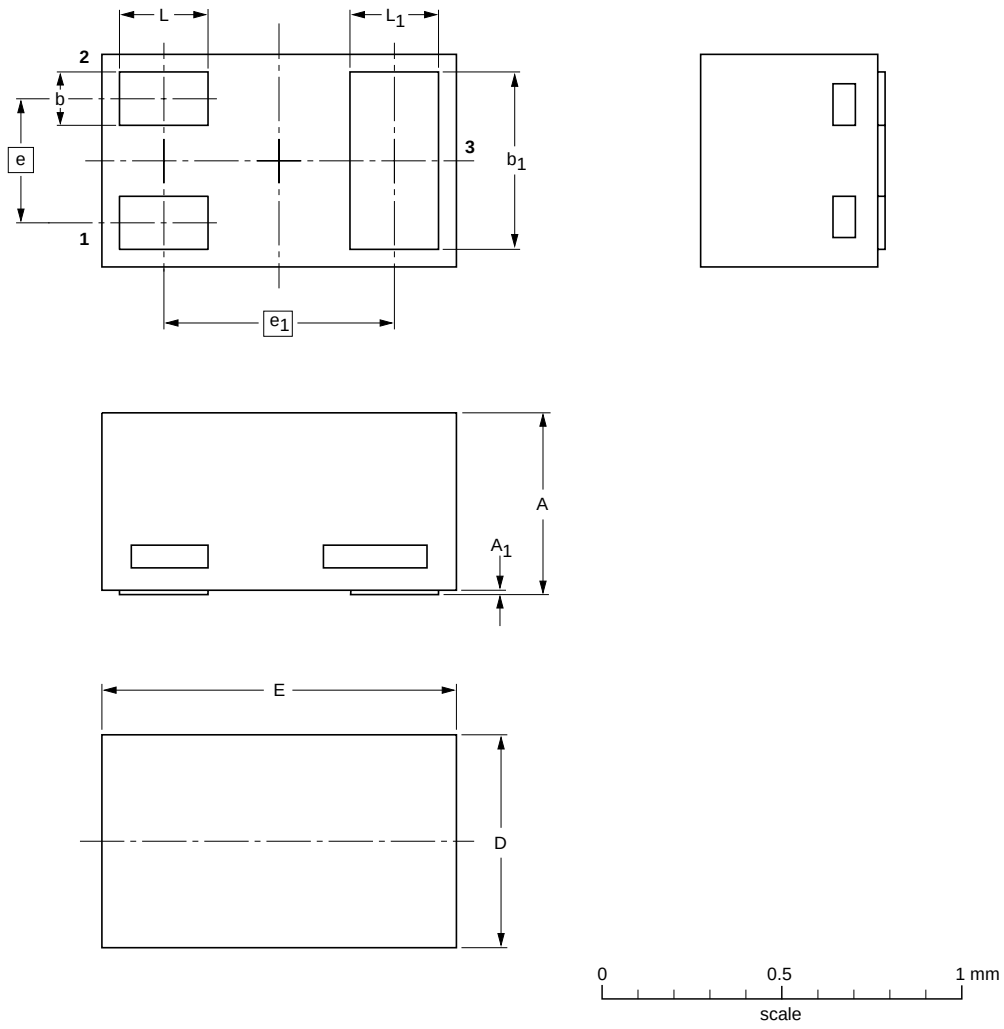
I_C/I_B = 20.

(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.7 Collector-emitter equivalent on-resistance as a function of collector current; typical values.

PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm **SOT883**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1)	A_1 max.	b	b_1	D	E	e	e_1	L	L_1
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT883			SC-101			~~03-02-05~~ 03-04-03

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

Contact information

For additional information please visit: **http://www.nxp.com**
For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

Printed in The Netherlands 613514/01/pp9 Date of release: 2003 Jul 22 Document order number: 9397 750 11558